

# Publications and Presentations by Mark Wistey

November 4, 2011

## Refereed Publications

1. W. Ha, V. Gambin, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "Long Wavelength GaInNAsSb/GaNAsSb Multiple Quantum Well Lasers," *Electron. Lett.*, Vol. 38, No. 6, pp. 277–8, Mar. 2002.
2. W. Ha, V. Gambin, M. Wistey, S. Bank, S. Kim, J. Harris, "Multiple Quantum Well GaInNAs/GaNAs Ridge-Waveguide Laser Diodes Operating Out to 1.4  $\mu\text{m}$ ," *IEEE Photon. Technol. Lett.*, Vol. 14, No. 5, May 2002.
3. V. Gambin, W. Ha, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "GaInNAsSb for 1.3–1.6  $\mu\text{m}$  Long-Wavelength Lasers Grown by Molecular Beam Epitaxy," *J. Select. Topics Quantum Electron.*, Vol. 8, No. 4, pp. 795–800, July 2002.
4. W. Ha, V. Gambin, M. Wistey, S. Bank, H. Yuen, S. Kim, J. Harris, "Long Wavelength GaInNAs(Sb) Lasers on GaAs," *J. Quantum Electron.*, Vol. 38, No. 9, pp. 1260–7, Sep. 2002.
5. V. Gambin, V. Lordi, W. Ha, M. Wistey, T. Takizawa, K. Uno, S. Friedrich, J. S. Harris, "Structural changes on annealing of MBE grown (Ga, In) (N, As) as measured by X-ray absorption fine structure," *J. Cryst. Growth*, Apr. 2003, Vol. 251, No. 1–4, p. 408–411.
6. S. Bank, W. Ha, V. Gambin, M. Wistey, H. Yuen, L. Goddard, J. S. Harris, "1.5- $\mu\text{m}$  GaInNAs(Sb) Lasers Grown on GaAs by MBE," *J. Cryst. Growth*, Vol. 251, pp. 367–371, 2003.
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10. S. R. Bank, M. A. Wistey, L. L. Goddard, H. B. Yuen, J. S. Harris, "Low Threshold, Continuous Wave, 1.5  $\mu\text{m}$  GaInNAsSb Lasers Grown on GaAs," *IEEE J. Quantum Electron.*, vol. 40, No. 6, pp. 656–664, June 2004.
11. M. A. Wistey, S. R. Bank, H. B. Yuen, L. L. Goddard, J. S. Harris, "GaInNAs(Sb) vertical-cavity surface-emitting lasers at 1.46 $\mu\text{m}$ ," *J. Vac. Sci. Technol.-B*, 22, No. 3, pp. 1562–1564, May/June 2004.
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27. S. R. Bank, M. A. Wistey, H. B. Yuen, L. L. Goddard, H. P. Bae, and J. S. Harris Jr., "Molecular-Beam Epitaxy Growth of Low-Threshold CW GaInNAsSb Lasers at 1.5  $\mu\text{m}$ ," *J. Vac. Sci. Technol.-B*, Vol. 23, No. 3, pp. 1337-40, May 2005.
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30. S. R. Bank, H. B. Yuen, M. A. Wistey, V. Lordi, H. P. Bae, and J. S. Harris, "Effects of growth temperature on the structural and optical properties of 1.55  $\mu\text{m}$  GaInNAsSb quantum wells grown on GaAs," *Appl. Phys. Lett.*, Vol. 87, No. 2, p. 21908-1-3, 11 July 2005.
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69. Rui Li, Yeqing Lu, Soo Doo Chae, Guangle Zhou, Qingmin Liu, Chen Chen, M. Shahriar Rahman, Tim Vasen, Qin Zhang, Patrick Fay, Tom Kosel, Mark Wistey, Huili (Grace) Xing, Siyuranga Koswatta and Alan Seabaugh, "InAs/AlGaSb heterojunction tunnel field-effect transistor with tunnelling in-line with the gate field," *Phys. Stat. Solidi*, TBD.
70. Zhou, G.; Lu, Y.; Li, R.; Zhang, Q.; Hwang, W. S.; Liu, Q.; Vasen, T.; Chen, C.; Zhu, H.; Kuo, J.-M.; Koswatta, S.; Kosel, T.; Wistey, M.; Fay, P.; Seabaugh, A.; Xing, H., "Vertical InGaAs/InP tunnel FETs with tunneling normal to the gate," *IEEE Electron Device Letters*, vol. PP, no. 99, p. 1-3.
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#### Book Chapters:

1. J. S. Harris, Jr., M. Wistey, S. Bank, L. Goddard, V. Lordi, H. Bae, H. Yuen, "Long-Wavelength Dilute Nitride-Antimonide Lasers," Chapter 17 in *Dilute Nitride (III-N-V) Semiconductors: Physics and Technology*, M. Henini, editor. Taylor & Francis, 2004.
2. J. S. Harris, Jr., H. Yuen, M. Wistey, S. Bank, V. Lordi, T. Gugov, H. Bae, L. Goddard, "MBE Growth and Characterization of Long Wavelength Dilute Nitride III-V Alloys," Chapter 1 in *Dilute Nitride (III-N-V) Semiconductors: Physics and Technology*, M. Henini, editor. Taylor & Francis, 2004.

#### Conference Presentations, Non-refereed Publications, and Invited Talks:

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